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11.1 Introduction

Sommario/riassunto

Crystals are the unacknowledged pillars of modern technology. The modern technological developments depend greatly on the availability of suitable single crystals, whether it is for lasers, semiconductors, magnetic devices, optical devices, superconductors, telecommunication, etc. In spite of great technological advancements in the recent years, we are still in the early stage with respect to the growth of several important crystals such as diamond, silicon carbide, PZT, gallium nitride, and so on. Unless the science of growing these crystals is understood precisely, it is impossible to grow t